

MS18N50

500V N-channel MOSFET

Description

The MS18N50 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220 package is universally preferred for all commercial-industrial applications

Features

- Originative New Design
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- 100% EAS Test
- Extended Safe Operating Area
- RoHS compliant package

Application

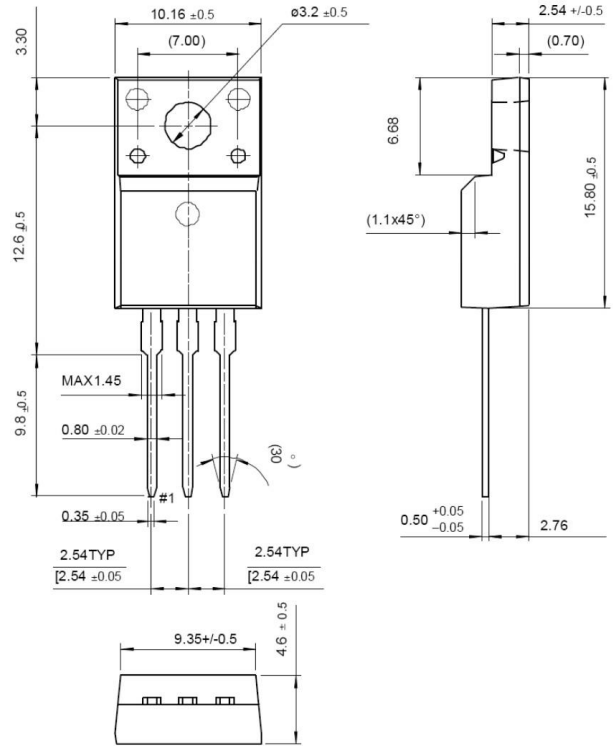
- High current, High speed switching
- PFC (Power Factor Correction)
- SMPS (Switched Mode Power Supplies)

Packing & Order Information

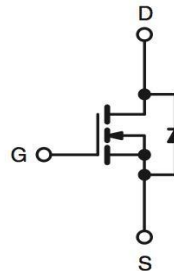
50/Tube ; 1,000/Box



**RoHS
COMPLIANT**



Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	500	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current -Continuous (TC=25°C)	18	A
	Drain Current -Continuous (TC=100°C)	10.8	A
I _{DM}	Drain Current -Pulsed	72	A
E _{AS}	Single Pulsed Avalanche Energy	990	mJ
E _{AR}	Repetitive Avalanche Energy	23.5	mJ
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns
T _J , T _{stg}	Operating Junction and Storage Temperature	-55~+150	°C
P _D	Power Dissipation (TC=25°C)	238	W
	Power Dissipation (TC=100°C)	1.8	W

- Drain current limited by maximum junction temperature

MS18N50

500V N-channel MOSFET

Thermal Characteristics

Symbol	Parameter	Value	Units
Rthjc	Thermal Resistance resistance	0.53	°C/W
RθJA	Thermal Resistance resistance	62.5	

Static Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
V_{GS}	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0		5.0	V
BV_{DSS}	$V_{GS} = 0 V, I_D = 250\mu A$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250\mu A$, Referenced to 25°C	--	0.6	--	V/°C
I_{DSS}	$V_{DS} = 500 V, V_{GS} = 0 V$ $V_{DS} = 400 V, V_{GS} = 0 V, T_C = 125^\circ C$	--	--	1 10	μA
I_{GSSF}	$V_{GS} = -30 V, V_{DS} = 0 V$	--	--	100	nA
I_{GSSR}	$V_{GS} = -30 V, V_{DS} = 0 V$			-100	nA
* $R_{DS(ON)}$	$V_{GS} = 10 V, I_D = 9 A$	--	0.25	0.32	Ω

Dynamic Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
C_{ISS}	$V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz$	--	2500	--	pF
C_{OSS}		--	400	--	pF
C_{RSS}		--	40	--	pF
$t_{d(on)}$	$V_{DD} = 250 V, I_D = 18 A, R_G = 25 \Omega$	--	70	--	ns
t_r		--	190	--	ns
$t_{d(off)}$		--	100	--	ns
t_f		--	100	--	ns
Q_g	$V_{DD} = 400 V, I_D = 18 A, V_{GS} = 10 V$	--	48.5	--	nC
Q_{gs}		--	14	--	nC
Q_{gd}		--	22	--	nC

Source-Drain Diode Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
I_S		--	--	18	A
I_{SM}		--	--	72	
V_{SD}	$I_S = 18 A, V_{GS} = 0 V$	--	--	1.5	V
t_{rr}	$I_F = 18 A, V_{GS} = 0 V$	--	550	--	ns
Q_{rr}	$diF/dt = 100 A/\mu s$	--	5.5	--	μC

MS18N50

500V N-channel MOSFET

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 5.5\text{mH}$, $I_{AS} = 18.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 16.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq \text{BVDSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

MS18N50

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■ Characteristic Curves

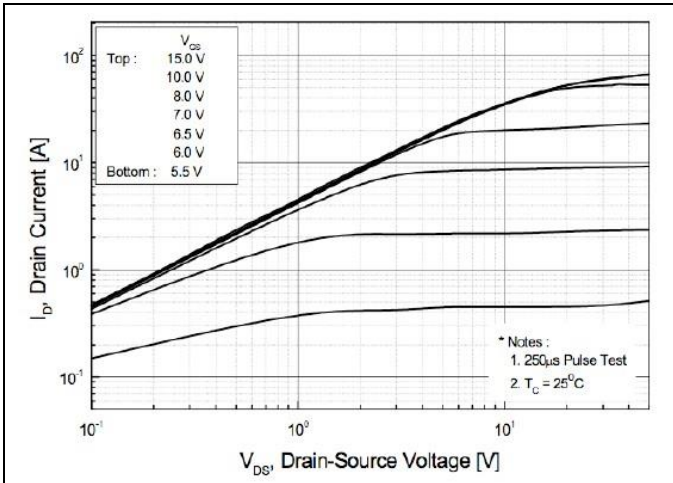


FIG.1-ON REGION CHARACTERISTICS

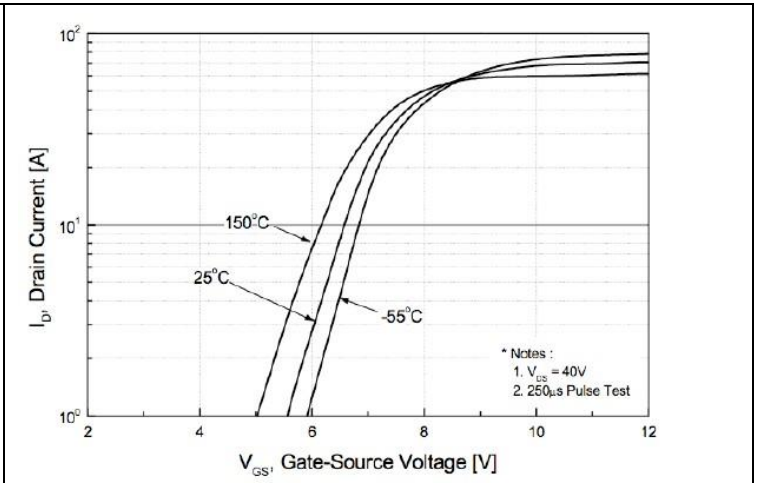


FIG.2-TRANSFER CHARACTERISTICS

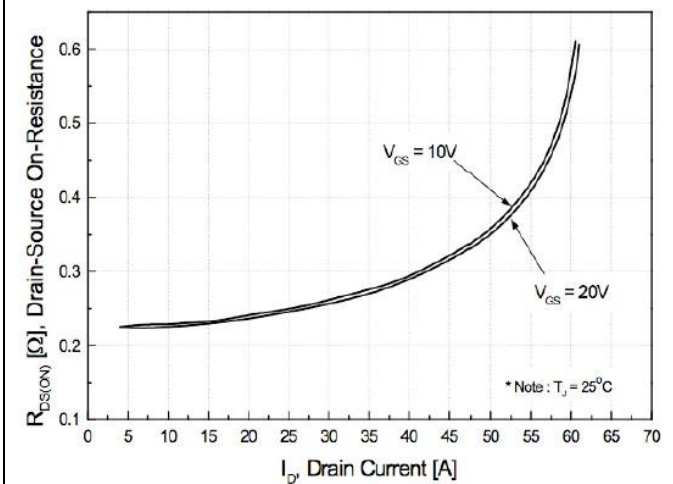


FIG.3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

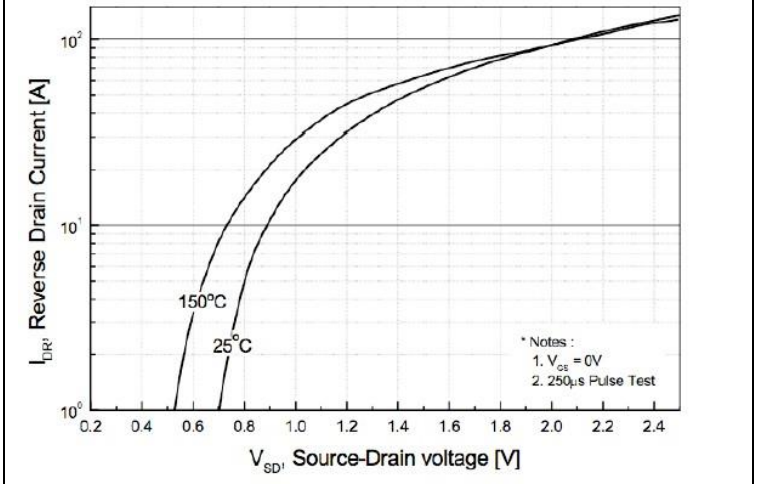


FIG.4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

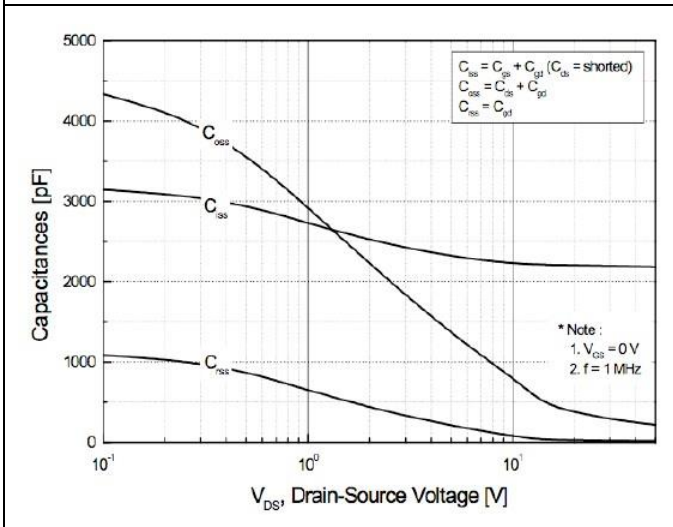


FIG.5-CAPACITANCE CHARACTERISTICS

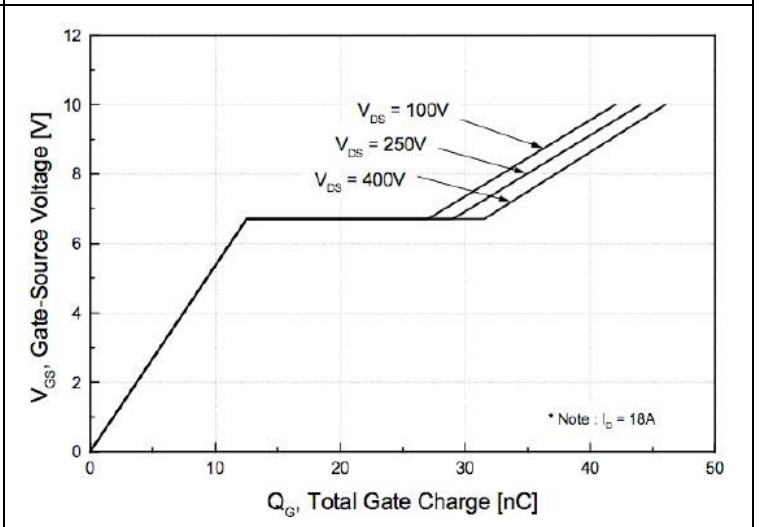


FIG.6-GATE CHARGE CHARACTERISTICS

MS18N50

500V N-channel MOSFET

Typical Electrical Characteristics

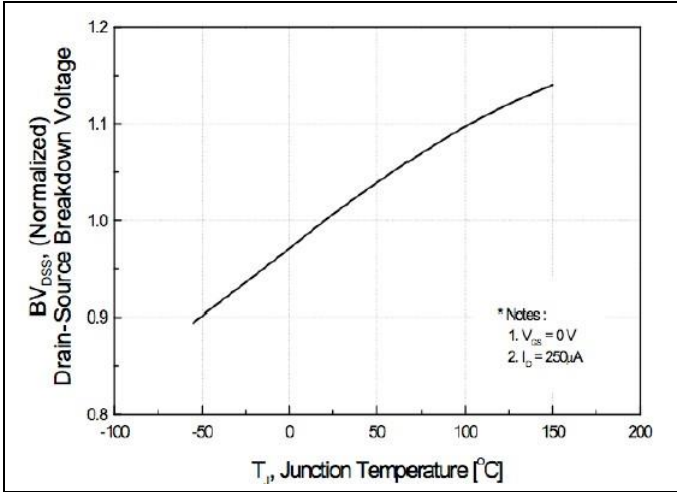


FIG.7-BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

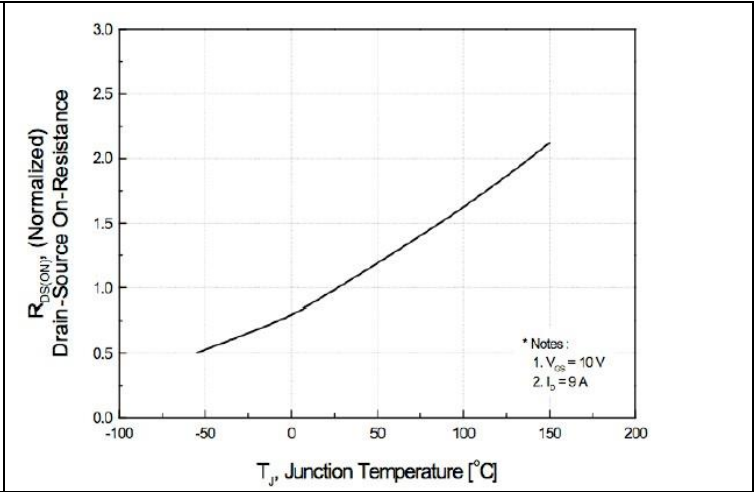


FIG.8-ON-RESISTANCE VARIATION VS TEMPERATURE

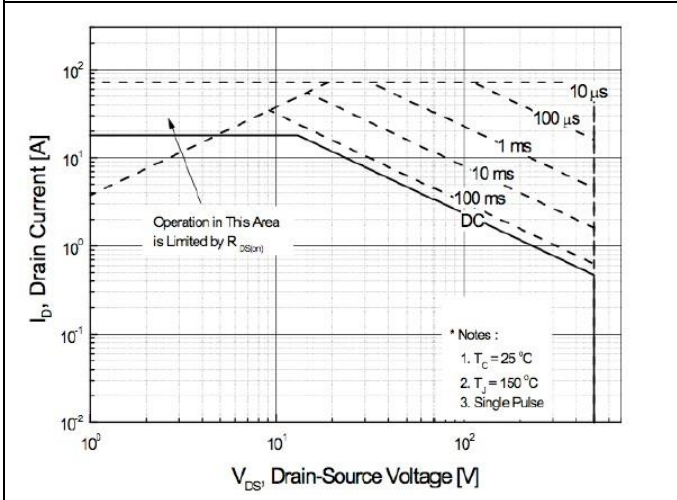


FIG.9-MAXIMUM SAFE OPERATING AREA

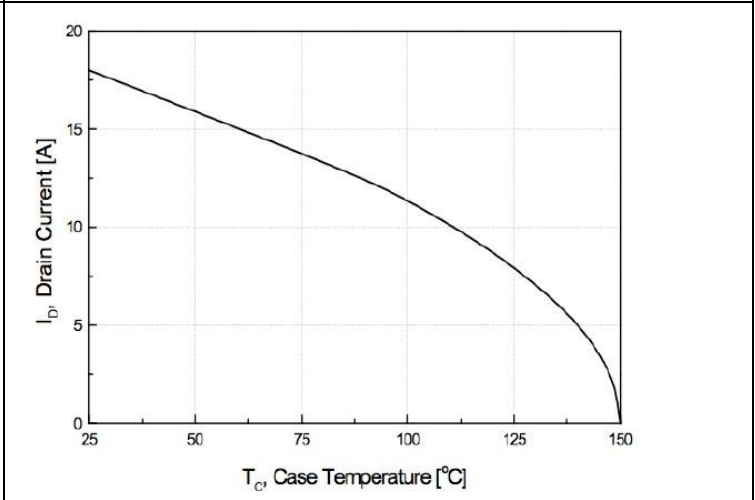


FIG.10-MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

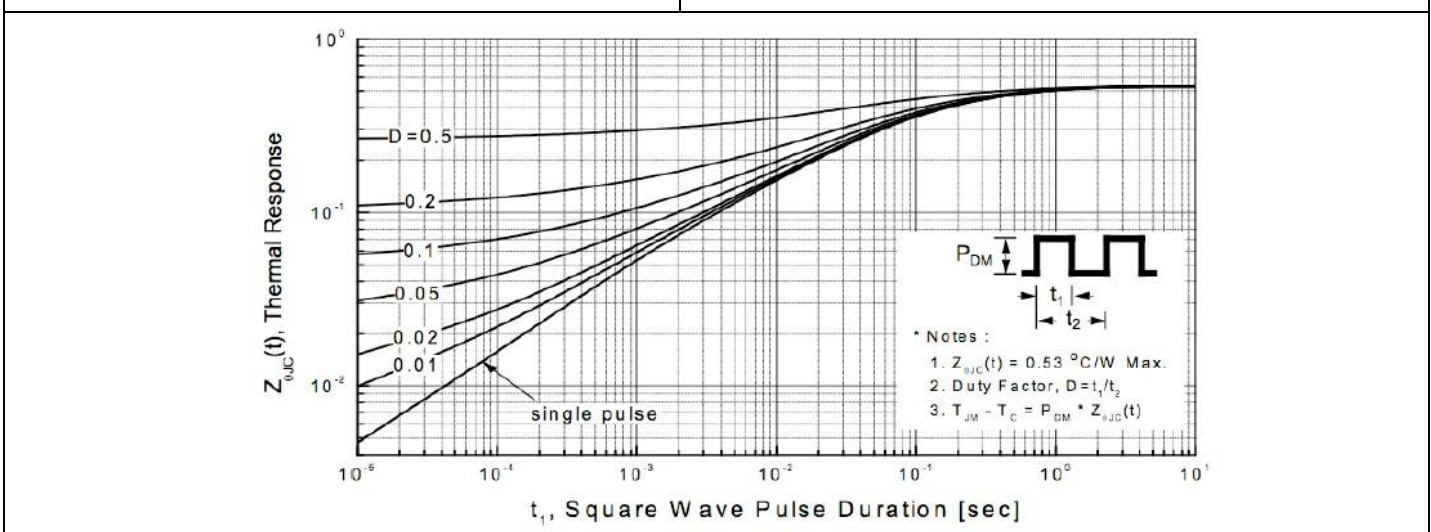


FIG.11-TRANSIENT THERMAL RESPONSE CURVE

MS18N50

500V N-channel MOSFET

■ Characteristics Test Circuit & Waveform

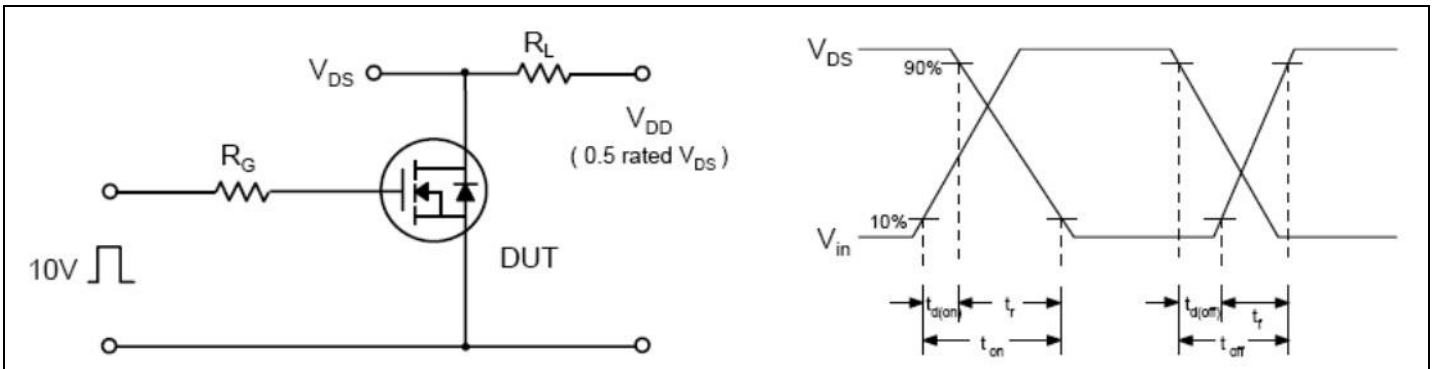


FIG.12-RESISTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

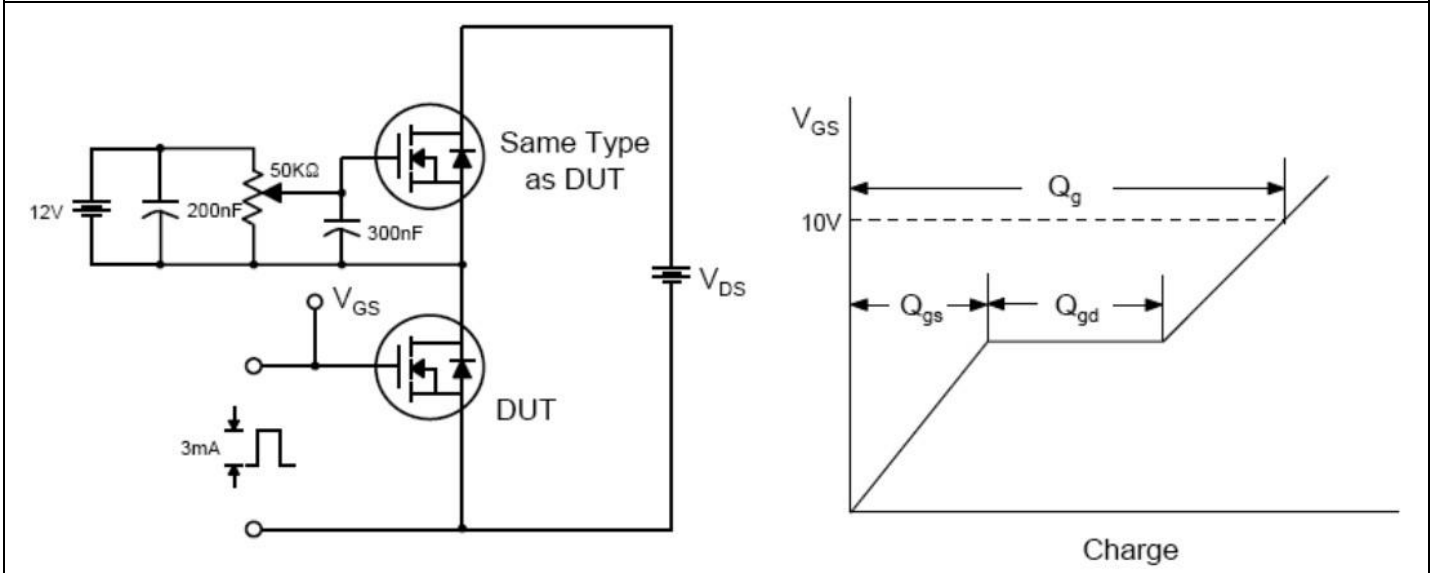


FIG.13-GATE CHARGE TEST CIRCUIT & WAVEFORM

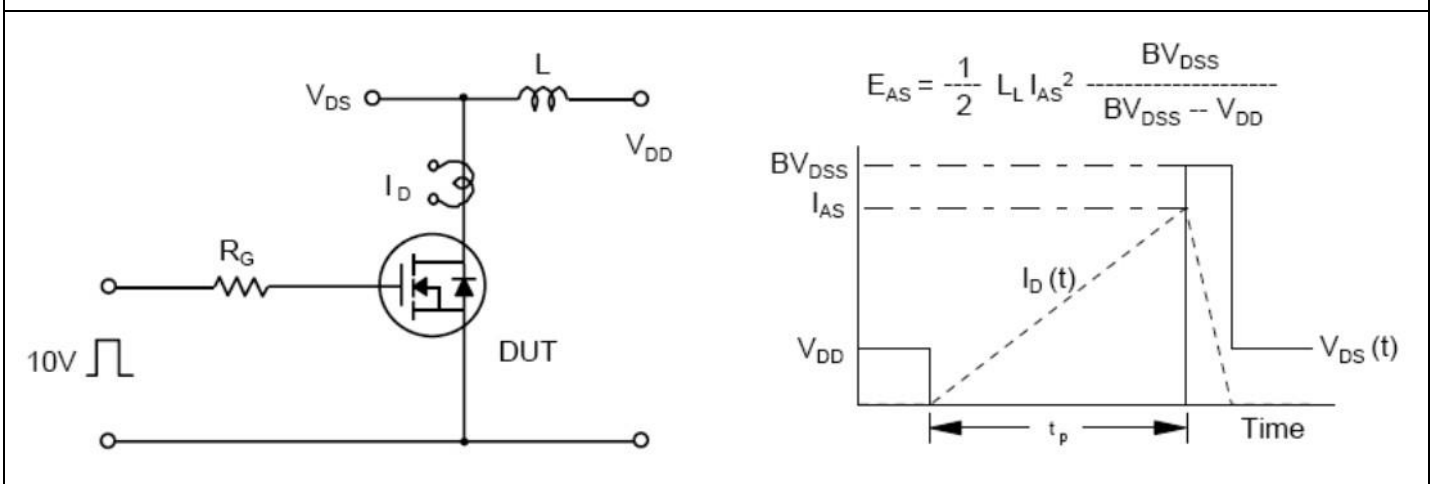


FIG.14-UNCLAMPED INDUCTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

MS18N50

500V N-channel MOSFET

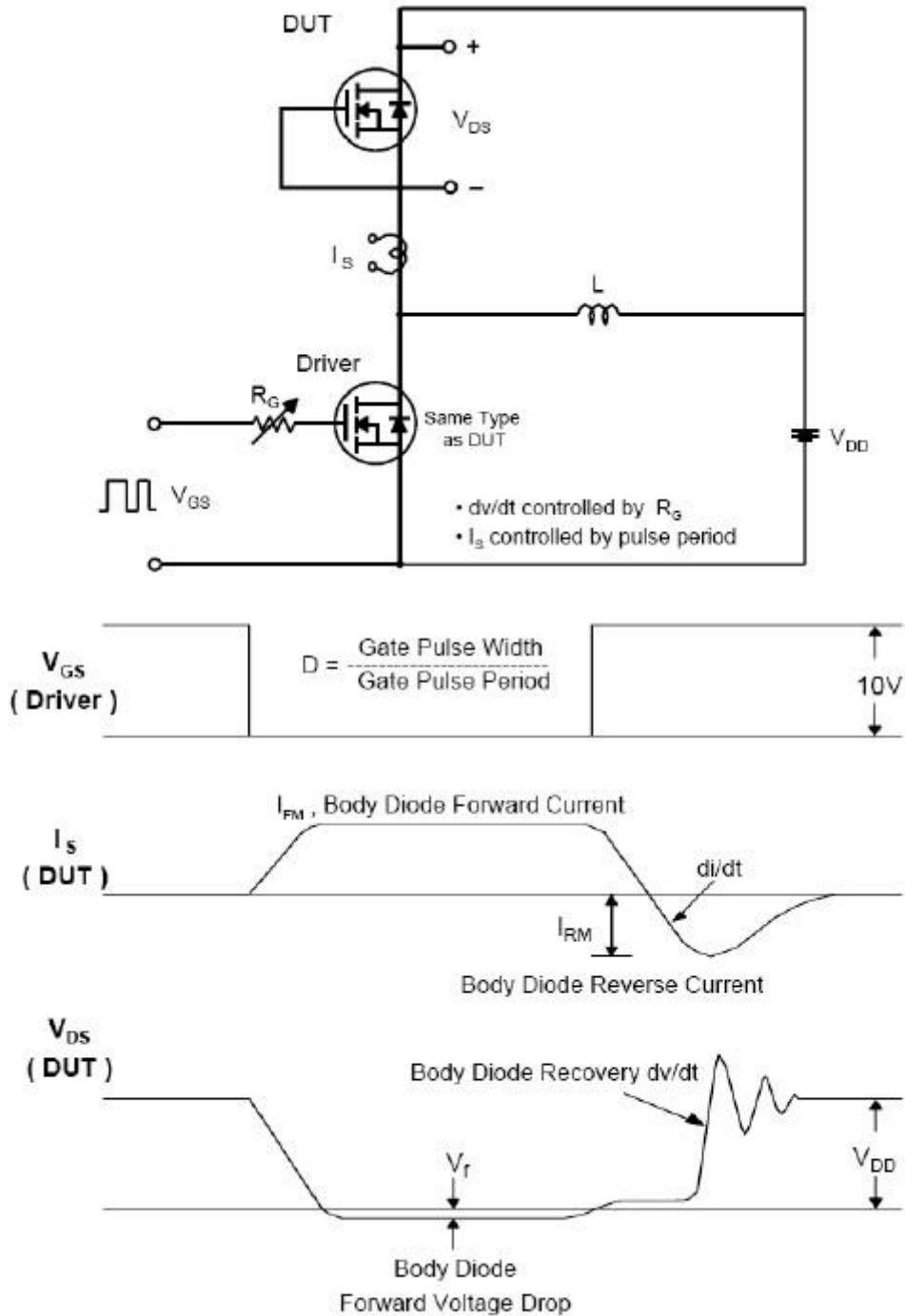


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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500V N-channel MOSFET

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